

1. General description

Silicon Carbide Schottky diode in a TO247-2L plastic package, designed for high frequency switched-mode power supplies.



2. Features and benefits

- Highly stable switching performance
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

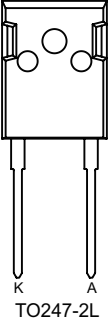
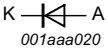
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values				Unit
Absolute maximum rating							
V _{RRM}	repetitive peak reverse voltage		650				V
I _{F(AV)}	average forward current	δ = 0.5 ; square-wave pulse; T _{mb} ≤ 85 °C; Fig. 1 ; Fig. 2 ; Fig. 3	10				A
T _j	junction temperature		175				°C
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; Fig. 5		-	1.5	1.7	V
		I _F = 10 A; T _j = 150 °C; Fig. 5		-	1.8	2.2	V
Dynamic characteristics							
Q _r	recovered charge	I _F = 10 A; dI _F /dt = 500 A/μs; V _R = 400 V; T _j = 25 °C; Fig. 7		-	14	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 TO247-2L	 001aaa020
2	A	anode		
mb	mb	mounting base; connected to cathode		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC2D10650W	TO247-2L	WNSC2D10650WQ	Tube	30	TO247L-2L	10-Nov-2020

7. Marking

Table 4. Marking codes

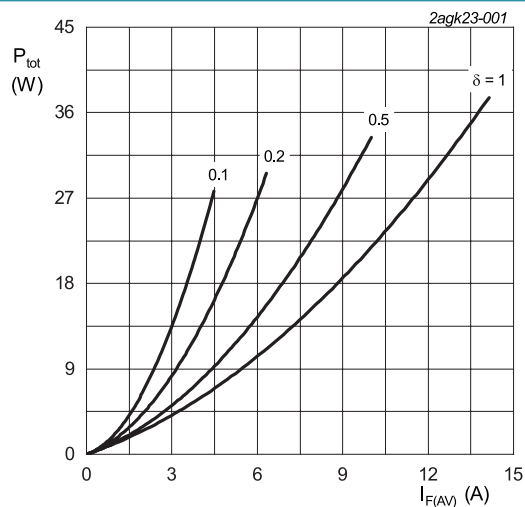
Type number	Marking codes
WNSC2D10650W	WNSC2D 10650W

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		650	V
V_{RWM}	crest working reverse voltage		650	V
V_R	reverse voltage	DC	650	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; square-wave pulse; $T_{mb} \leq 85^\circ\text{C}$; Fig. 1; Fig. 2; Fig. 3	10	A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25\ \mu\text{s}$; $T_{mb} \leq 85^\circ\text{C}$; square-wave pulse	20	A
I_{FSM}	non-repetitive peak forward current	$t_p = 10\ \text{ms}$; $T_{j(\text{init})} = 25^\circ\text{C}$; sine-wave pulse	50	A
		$t_p = 10\ \mu\text{s}$; $T_{j(\text{init})} = 25^\circ\text{C}$; square-wave pulse	450	A
I^2t	I^2t for fusing	sine-wave pulse; $T_{j(\text{init})} = 25^\circ\text{C}$; $t_p = 10\ \text{ms}$	12.5	A^2s
T_{stg}	storage temperature		-55 to 175	$^\circ\text{C}$
T_j	junction temperature		175	$^\circ\text{C}$



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 1.024\ \text{V}; R_s = 0.1156\ \Omega$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

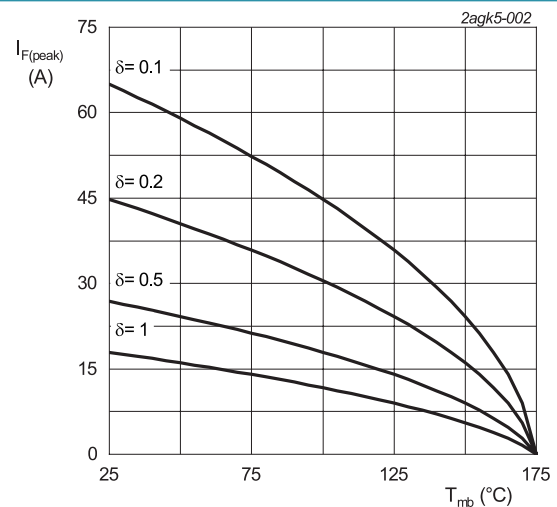


Fig. 2. Current derating as a function of mounting base temperature

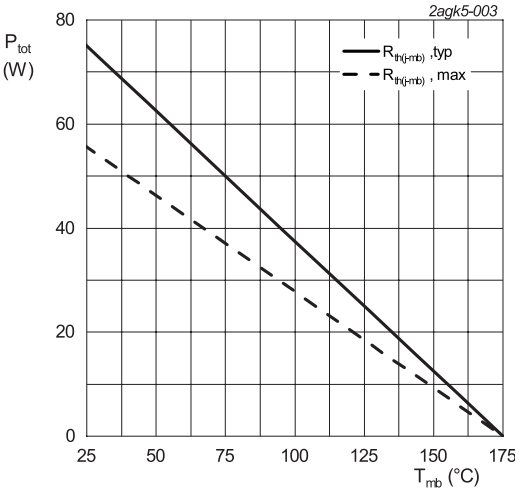


Fig. 3. Total power dissipation as a function of mounting base temperature

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4		-	-	2.7	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	50	-	K/W

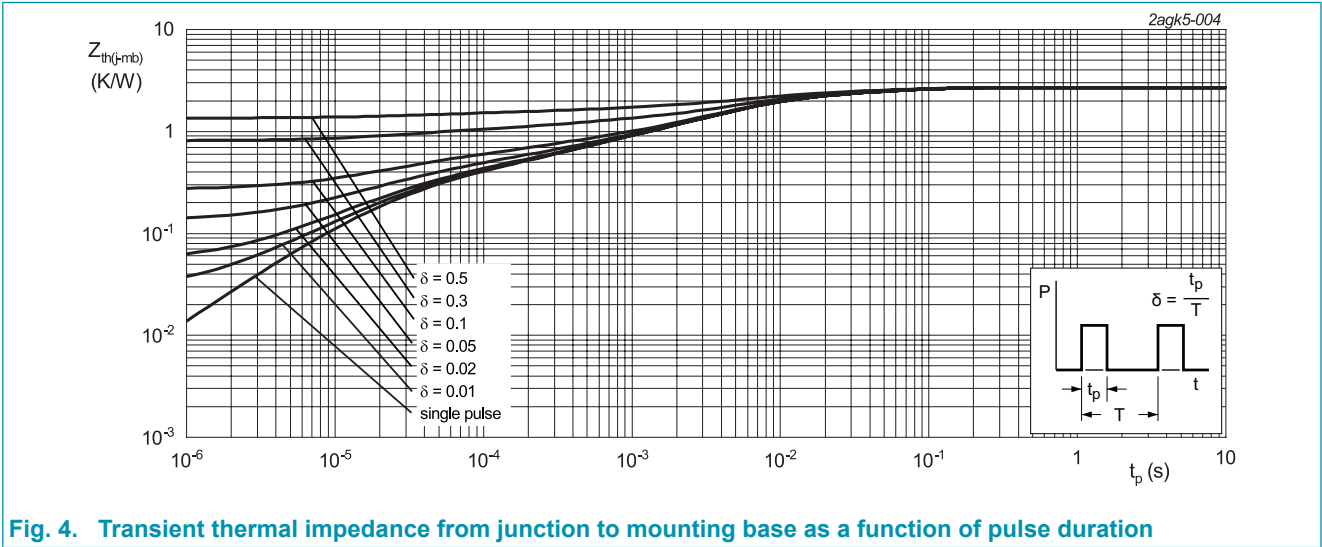
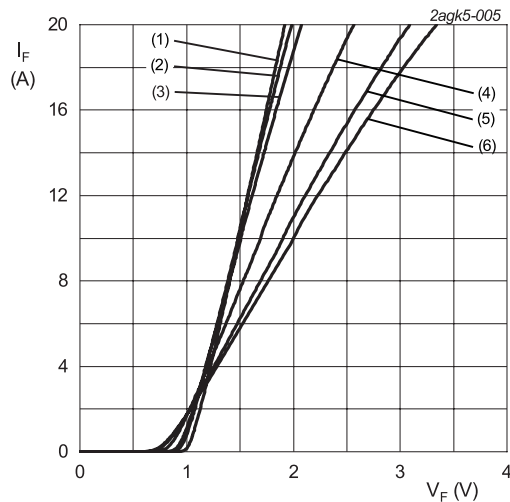


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V _F	forward current	I _F = 10 A; T _J = 25 °C; Fig. 5		-	1.5	1.7	V
		I _F = 10 A; T _J = 150 °C; Fig. 5		-	1.8	2.2	V
		I _F = 10 A; T _J = 175 °C; Fig. 5		-	2	2.3	V
I _R	reverse current	V _R = 650 V; T _J = 25 °C; Fig. 6		-	0.5	50	μA
		V _R = 650 V; T _J = 175 °C; Fig. 6		-	25	250	μA
Dynamic characteristics							
Q _r	recovered charge	I _F = 10 A; V _R = 400 V; dI _F /dt = 500 A/μs; T _J = 25 °C; Fig. 7		-	14	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _J = 25 °C		-	310	-	pF
		f = 1 MHz; V _R = 300 V; T _J = 25 °C		-	36	-	pF
		f = 1 MHz; V _R = 600 V; T _J = 25 °C		-	32	-	pF
E _{as}	non-repetitive avalanche energy	I _R = 5.5 A; L = 5 mH; T _J (init) = 25 °C		75	-	-	mJ



$V_o = 1.024\text{ V}; R_s = 0.1156\text{ }\Omega$

- (1) $T_J = -55\text{ }^\circ\text{C}$; typical values
- (2) $T_J = 0\text{ }^\circ\text{C}$; typical values
- (3) $T_J = 25\text{ }^\circ\text{C}$; typical values
- (4) $T_J = 100\text{ }^\circ\text{C}$; typical values
- (5) $T_J = 150\text{ }^\circ\text{C}$; typical values
- (6) $T_J = 175\text{ }^\circ\text{C}$; typical values

Fig. 5. Forward current as a function of forward voltage; typical values

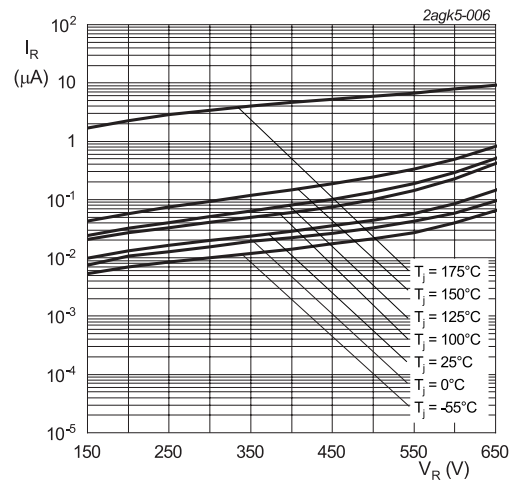


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

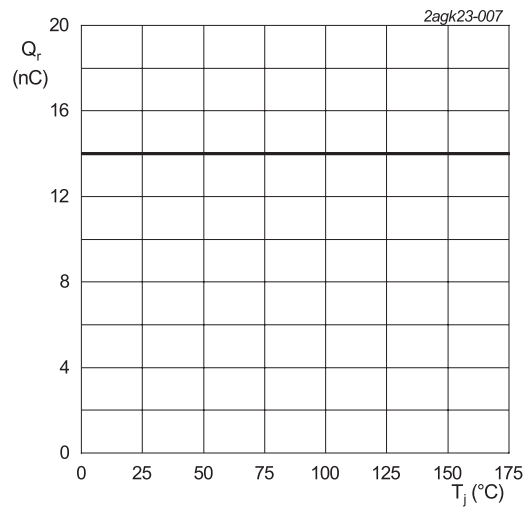


Fig. 7. Recovered charge as a function of junction temperature

11. Package outline

Plastic single-ended through-hole package; heatsink mounted;1 mounting hole; 2 leads TO-247

TO247-2L

The technical drawing illustrates the package outline for the WNSC2D10650W diode. It includes three views: a top view showing the mounting hole (Ø) and leads (p, q); a side view showing the package height (A, A1) and lead length (L, L1); and a front view showing the package width (E1, E2, E3) and lead spacing (b, b1). Dimensions are labeled with letters and numbers, and specific values are provided in the table below.

UNIT	A	A ₁	b	b ₁	c	D	D ₁	D ₂	E	E ₁	E ₂	E ₃	e	L	L ₁	P ₂	p	Q	q	Ø
mm	5.20	2.10	1.40	2.20	0.70	20.60	16.20	1.20	15.75	14.22	5.20	1.80	10.90	20.72	4.75	3.60	3.70	2.60	6.18	7.30
	4.70	1.90	1.00	1.80	0.50	20.30	16.87	0.80	15.45	13.82	4.80	1.40	BSC	20.22	4.25	3.40	3.50	2.20	5.78	7.10

Note:

- Mold resin protrusion max 0.127mm.
- Metal exposed with Sn plating.

12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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